

HiPerFRED²

DPG10I200PA

V_{RRM}	=	200 V
I _{fav}	=	10 A
t _{rr}	=	35 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

Part number

DPG10I200PA



Package: TO-220

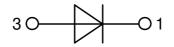
RoHS compliant

• Industry standard outline

• Epoxy meets UL 94V-0

Backside: cathode

20200211b



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littlefuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littlefuse.com/disclaimer-electronics.

IXYS reserves the right to change limits, conditions and dimensions.



DPG10I200PA

Fast Dio	de				Ratings	6	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blockir	ng voltage	$T_{VJ} = 25^{\circ}C$			200	V
V _{RRM}	max. repetitive reverse blocking vo	ltage	$T_{vJ} = 25^{\circ}C$			200	V
I _R	reverse current, drain current	$V_R = 200 V$	$T_{VJ} = 25^{\circ}C$			1	μA
		V_{R} = 200 V	$T_{vJ} = 150^{\circ}C$			0.06	mA
V _F	forward voltage drop	I _F = 10 A	$T_{vJ} = 25^{\circ}C$			1.27	V
		I _F = 20 A				1.45	V
		I _F = 10 A	T _{vJ} = 150°C			0.98	V
		$I_{F} = 20 \text{ A}$				1.17	V
I FAV	average forward current	T _c = 150°C	T _{vJ} = 175°C			10	А
		rectangular d = 0.5					
V _{F0}	threshold voltage		$T_{vJ} = 175^{\circ}C$			0.74	V
r _F	slope resistance } for power los	ss calculation only				17.7	mΩ
R _{thJC}	thermal resistance junction to case					2.3	K/W
R _{thCH}	thermal resistance case to heatsing	k			0.5		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			65	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_{R} = 0 \text{ V}$	$T_{vJ} = 45^{\circ}C$			140	Α
C	junction capacitance	$V_{R} = 150 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		15		pF
I _{RM}	max. reverse recovery current		$T_{VJ} = 25 °C$		3		Α
		$I_F = 10 \text{ A}; V_R = 130 \text{ V}$	T _{vJ} = 125 °C		5.5		Α
t _{rr}	reverse recovery time	$I_F = 10 \text{ A}; V_R = 130 \text{ V}$ - $di_F / dt = 200 \text{ A}/\mu\text{s}$	$T_{VJ} = 25 \degree C$		35		ns
)		$T_{vJ} = 125 ^{\circ}\text{C}$		45		ns

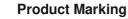
IXYS reserves the right to change limits, conditions and dimensions.

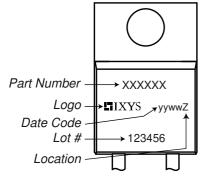
20200211b



DPG10I200PA

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal			35	Α
T_{vJ}	virtual junction temperature		-55		175	°C
T _{op}	operation temperature		-55		150	°C
T _{stg}	storage temperature		-55		150	°C
Weight				2		g
M _D	mounting torque		0.4		0.6	Nm
F _c	mounting force with clip		20		60	Ν





Part description

- D = Diode
- P = HiPerFREDG = extreme fast
- 10 = Current Rating [A]
- I = Single Diode
- 200 = Reverse Voltage [V]
- PA = TO-220AC (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG10I200PA	DPG10I200PA	Tube	50	506301

Similar Part	Package	Voltage class
DPG10I200PM	TO-220ACFP (2)	200

Equivalent Circuits for Simulation		* on die level	$T_{VJ} = 175^{\circ}C$	
	$-R_{o}-$	Fast Diode		
V _{0 max}	threshold voltage	0.74		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	14.5		mΩ

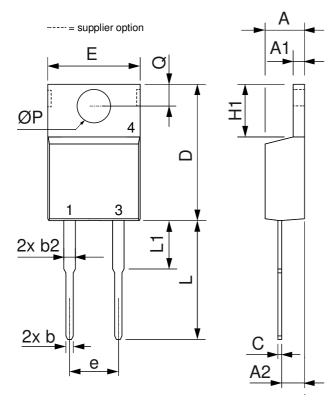
IXYS reserves the right to change limits, conditions and dimensions.

20200211b

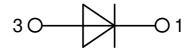


DPG10I200PA

Outlines TO-220



Dim.	Millir	neter	Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
С	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
е	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



IXYS reserves the right to change limits, conditions and dimensions.